

### **INCHANGE SEMICONDUCTOR**

### isc N-Channel MOSFET Transistor

## 2SK1039

#### DESCRIPTION

- Drain Current  $-I_D$ =8A@  $T_C$ =25  $^{\circ}C$
- Drain Source Voltage-: V<sub>DSS</sub>=400V(Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

ADCOLUTE MAXIMUM DATINCOT -25°0

#### APPLICATIONS

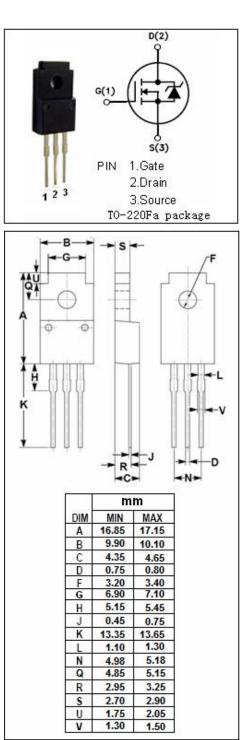
Designed for high voltage, high speed power switching

| ABSOLUT          | E MAXIMUM RATINGS(T <sub>a</sub> =25°C)   |         |      |
|------------------|---|---------|------|
| SYMBOL           | ARAMETER                                  | VALUE   | UNIT |
| VDSS             | Drain-Source Voltage (V <sub>GS</sub> =0) | 400     | V    |
| V <sub>GS</sub>  | Gate-Source Voltage                       | ±20     | V    |
| ID               | Drain Current-continuous@ TC=25°C         | 8       | А    |
| P <sub>tot</sub> | Total Dissipation@TC=25°C                 | 50      | W    |
| Tj               | Max. Operating Junction Temperature       | 150     | °C   |
| T <sub>stg</sub> | Storage Temperature Range                 | -55~150 | °C   |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                               | МАХ  | UNIT |
|---------------------|---|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case    | 0.83 | °C/W |
| R <sub>th j-a</sub> | Thermal Resistance, Junction to Ambient | 35   | °C/W |

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|                            | ELECTRICAL CHARACTERISTICS (TC=25 C) |  |     |     |      |      |  |  |  |
|----------------------------|--------------------------------------|--|-----|-----|------|------|--|--|--|
| SYMBOL                     | PARAMETER                            | CONDITIONS                                 | MIN | ТҮР | МАХ  | UNIT |  |  |  |
| V <sub>(BR)DSS</sub>       | Drain-Source Breakdown Voltage       | V <sub>GS</sub> =0; I <sub>D</sub> = 10mA  | 400 |     |      | V    |  |  |  |
| V <sub>GS(th)</sub>        | Gate Threshold Voltage               | V <sub>DS</sub> =0; I <sub>D</sub> =1mA    | 1.0 |     | 5.0  | V    |  |  |  |
| $R_{\text{DS}(\text{on})}$ | Drain-Source On-stage Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =5A   |     |     | 1.4  | Ω    |  |  |  |
| I <sub>GSS</sub>           | Gate Source Leakage Current          | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0 |     |     | ±100 | nA   |  |  |  |
| IDSS                       | Zero Gate Voltage Drain Current      | V <sub>DS</sub> =400V; V <sub>GS</sub> = 0 |     |     | 500  | uA   |  |  |  |

#### • ELECTRICAL CHARACTERISTICS (Tc=25°C)

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